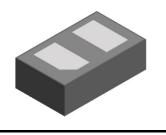


Bi-directional 3.3V Normal Capacitance ESD Protector

Description

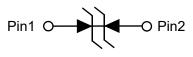
The PESDNC2FD3V3BA protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, low operating voltage. It gives designer the flexibility to protect one bi-directional line in applications where arrays are not practical.



DFN1006-2L(Bottom View)

Feature

- \triangleright 90W peak pulse power per line (t_p = 8/20µs)
- ➤ DFN1006-2L package
- Response time is typically < 1 ns</p>
- > Bidirectional configurations
- ➤ Low clamping voltage
- > RoHS compliant
- ➤ Transient protection for data lines to IEC 61000-4-2(ESD) ±30kV(air), ± 30kV(contact); IEC 61000-4-5 (Lightning) 10A (8/20us)



Circuit Diagram



Marking (Top View)

Applications

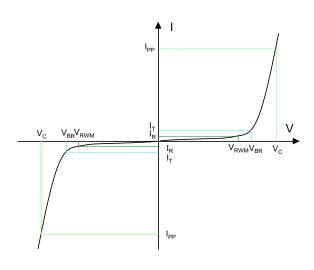
- Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- ➤ Portable instrumentation
- Cordless phones
- Digital cameras
- > Peripherals

Mechanical Characteristics

- Mounting position: Any
- Qualified max reflow temperature:260°C
- > Device meets MSL 1 requirements
- ➤ DFN1006-2L without plating

Electronics Parameter

Symbol	Parameter			
V_{RWM}	Peak Reverse Working Voltage			
I _R	Reverse Leakage Current @ V _{RWM}			
V _{BR}	Breakdown Voltage @ I _T			
I _T	Test Current			
I _{PP}	Maximum Reverse Peak Pulse Current			
V _C	Clamping Voltage @ I _{PP}			
P _{PP}	Peak Pulse Power			
CJ	Junction Capacitance			
I _F	Forward Current			
V _F	Forward Voltage @ I _F			



Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V _{RWM}	-	-	-	3.3	V
Breakdown Voltage	V_{BR}	I _t = 1mA	4	-	6.5	V
Reverse Leakage Current	I _R	V _{RWM} = 3.3V	-	-	1	μA
Clamping Voltage ¹⁾	V _C	TLP = 16A, $t_p = 100 \text{ns}$	-	8.5	-	V
Dynamic resistance ¹⁾	R _{DYN}	-	-	0.15	-	Ω
Clamping Valtage?)	V _c	$I_{PP} = 1A, t_P = 8/20 \mu s$	-	6.5	8	V
Clamping Voltage ²⁾		$I_{PP} = 10A, t_P = 8/20\mu s$	-	8.5	10.5	V
Junction Capacitance	CJ	$V_R = 0V, f = 1MHz$	-	21	-	pF

Notes:

Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Peak Pulse Power (t _P = 8/20µs)	P _{PP}	90	W
Peak Pulse Current (t _P = 8/20μs)	I _{PP}	10	А
Lead Soldering Temperature	T _L	260 (10 sec)	℃
Junction and Storage Temperature Range	$T_{J,}T_{STG}$	-55~+150	°C
ESD Protection-Contact Discharge	V _{ESD}	±30	kV
ESD Protection-Air Discharge	V _{ESD}	±30	kV

^{1.}TLP parameter: Z_0 =50 Ω , t_p =100ns, t_r =2ns, averaging window from 60ns to 80ns. R_{DYN} is calculated from 4A to 16A. 2.Non-repetitive current pulse, according to IEC61000-4-5.

Typical Characteristics

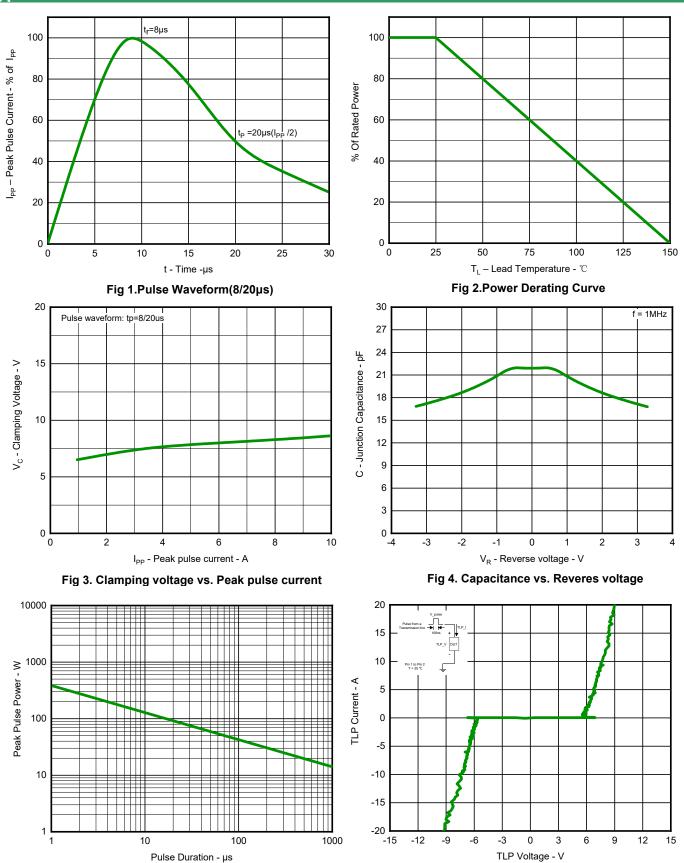


Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time

Fig 6. TLP Measurement

ESD Protector

PESDNC2FD3V3BA

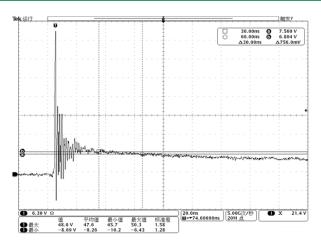


Fig 7. Clamping Voltage at IEC61000-4-2 +8kV Pulse Waveform

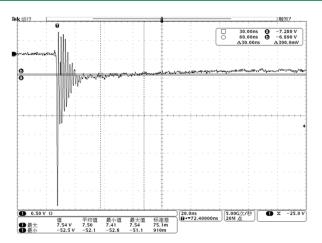
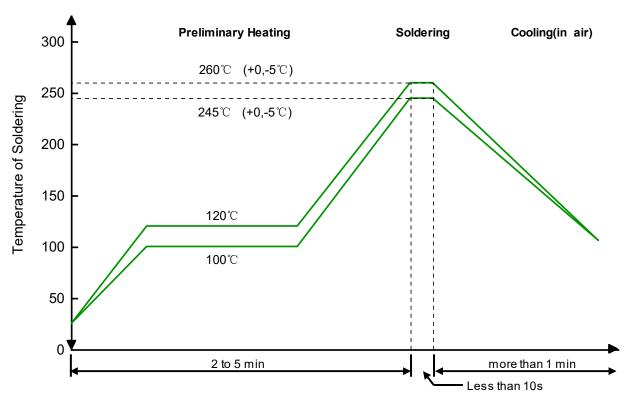


Fig 8. Clamping Voltage at IEC61000-4-2 -8kV Pulse Waveform

Solder Reflow Recommendation



Remark: Pb free for 260°C; Pb for 245°C.

PCB Design

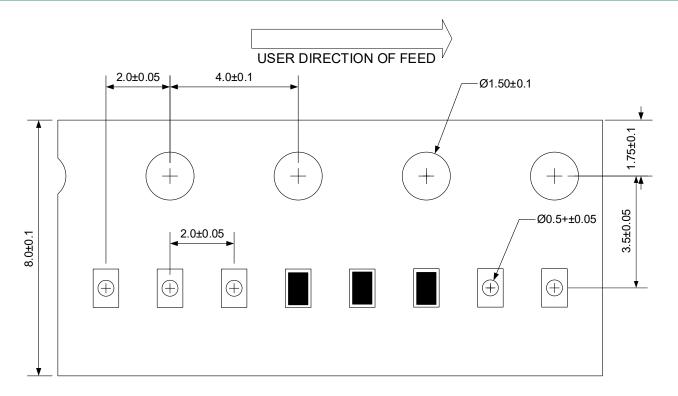
For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- > Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- Do not make false economies and save copper for the ground connection.
- > Place via holes to ground as close as possible to the anode of the TVS diode.
- Use as many via holes as possible for the ground connection.
- > Keep the length of via holes in mind! The longer the more inductance they will have.

Ordering information

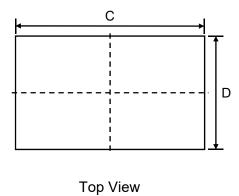
Device	Package	Reel	Shipping
PESDNC2FD3V3BA	DFN1006-2L (Pb-Free)	7"	10000 / Tape & Reel

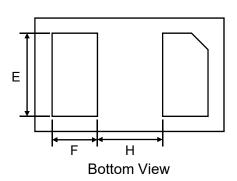
Load with information

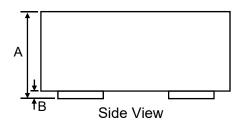


Unit:mm

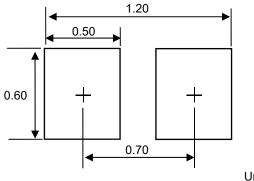
Product dimension (DFN1006-2L)







Dim	Millimeters		Inches		
	Min	Max	Min	Max	
Α	0.340	0.498	0.013	0.020	
В	0.000	0.050	0.000	0.002	
С	0.950	1.080	0.037	0.043	
D	0.550	0.680	0.022	0.027	
Е	0.400	0.600	0.016	0.024	
F	0.200	0.300	0.008	0.012	
Н	0.400 Typ.		0.015 Typ.		



Unit:mm

Suggested PCB Layout

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